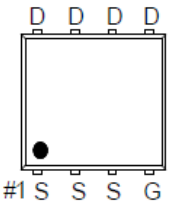
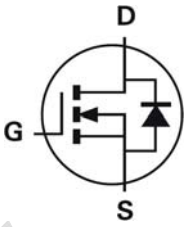
DG100N16S

DG-FET™ 100V N-Channel Power MOSFET

Key Performance Parameters		
Parameter	Value	Unit
V_{DSS}	100	V
$R_{DS(ON)\ max.}$ V_{GS}=10V	8	mΩ
I_D	24.8	A
Q_g	56.2	nC
Q_{gd}	14.4	nC
Q_{SW}	19.9	nC

SOP-8





Features	Application
• Optimized for synchronous rectification Low Input Capacitance • Low Miller Capacitance • Fully Characterized Capacitance and Avalanche • Pb-free lead plating; RoHS compliant	• BLDC Motor drive applications • Battery powered circuits • Synchronous rectifier applications • Resonant mode power supplies

Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
DG100N16S	Halogen-Free	SOP-8	S	Tape & Reel	3,000

Absolute Maximum Ratings (T_J=25°C unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	±20	V
Drain Current-Continuous	T_C=25°C	I_D	24.8	A
	T_C=100°C		15.7	A
Drain Current-Pulsed Note 1	T_C=25°C	I_{DM}	62.5	A
Avalanche Current		I_{AR}	9.0	A
Single Pulse Avalanche Energy Note 3		E_{AS}	4.1	mJ
Maximum Power Dissipation	T_C=25°C	P_{tot}	10.8	W
Operating Junction Temperature Range		T_J	150	°C

Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Junction-to-Ambient Note 2	$R_{\theta JA}$	Steady State	-	41.8		°C/W
Thermal resistance, Junction-to-Case	$R_{\theta JC}$	Steady State	-	11.6		°C/W

Notes:

1. Pulse Test: Pulse Width ≤ 10ms, Duty Cycle ≤ 1%.
2. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. For surface-mounted packages, both $R_{\theta JA}$ and $R_{\theta JC}$ are measured with the device mounted on approximately 1"×1" FR-4 PCB. In actual applications, the PCB layout may greatly affect the thermal resistance and current-carrying capability of the device-board assembly.
3. Starting T_J=25°C, VD=50V, L=0.1mH, Rg=50Ω, V_{GS}=10V.

Electrical Characteristics (T_J=25°C unless otherwise noted)

STATIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_{DS}=10mA	100	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=100V, V_{GS}=0V, T_J=25°C	-	-	10	µA
		V_{DS}=100V, V_{GS}=0V, T_J=125°C	-	-	100	µA
Gate-Body Leakage	I_{GSS}	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA

STATIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS}=V_{GS}, I_{DS}=250µA	1.2	-	2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_{DS}=10A	-	-	8	mΩ
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=4.5V, I_{DS}=7A	-	-	10.1	mΩ
Gate Resistance	R_g	V_{GS}=0V, V_{DS}=0V, f=1MHz	-	0.66	-	Ω
Forward Transconductance	g_{fs}	V_{DS}=5V, I_{DS}=20A	-	34	-	S

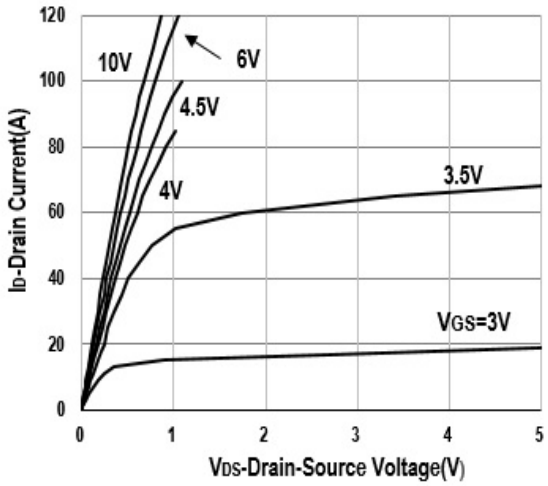
DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Input Capacitance	C_{iss}	V_{DS}=50V, V_{GS}=0V, f=1MHz	-	2561	-	pF
Output Capacitance	C_{oss}	V_{DS}=50V, V_{GS}=0V, f=1MHz	-	355	-	pF
Reverse Transfer Capacitance	C_{rss}	V_{DS}=50V, V_{GS}=0V, f=1MHz	-	13	-	pF
Turn-On Delay Time	$T_{d(on)}$	V_{DS}=50V, V_{GS}=10V, I_{DS}=45A, R_{GEN}=3.6Ω	-	10.4	-	ns
Rise Time	t_r	V_{DS}=50V, V_{GS}=10V, I_{DS}=45A, R_{GEN}=3.6Ω	-	21.7	-	ns
Turn-Off Delay Time	$T_{d(off)}$	V_{DS}=50V, V_{GS}=10V, I_{DS}=45A, R_{GEN}=3.6Ω	-	40.5	-	ns
Fall Time	t_f	V_{DS}=50V, V_{GS}=10V, I_{DS}=45A, R_{GEN}=3.6Ω	-	29.1	-	ns

GATE CHARGE CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Gate to Source Gate Charge	Q_{gs}	V_{DD}=50V, I_D=20A,	-	10.3	-	nC
Gate charge at threshold	$Q_{g(th)}$	V_{DD}=50V, I_D=20A,	-	4.7	-	nC
Gate to Drain Charge	Q_{gd}	V_{DD}=50V, I_D=20A,	-	14.4	-	nC
Switching charge	Q_{SW}	V_{DD}=50V, I_D=20A,	-	19.9	-	nC
Gate charge total	Q_g	V_{DD}=50V, I_D=20A, V_{GS}=0 to 10V	-	56.2	-	nC
Gate plateau voltage	$V_{plateau}$	V_{DD}=50V	-	3.5	-	V
Gate charge total, sync. FET (Q_g- Q_{gd})	$Q_{g(sync)}$	V_{DS}=0.1V	-	41.8	-	nC

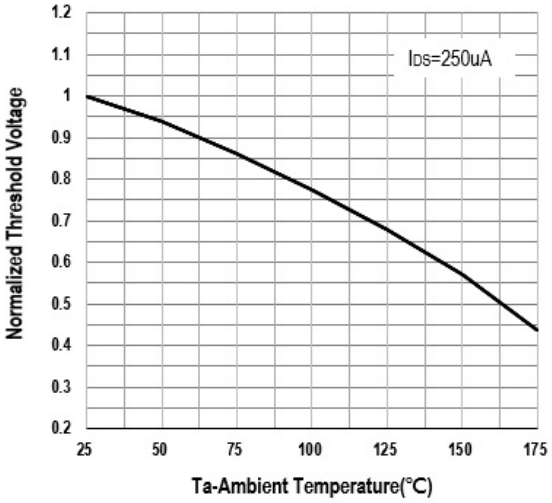
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_F=20A	-	0.7	1.3	V
Body Diode Reverse Recovery Time	t_{rr}	V_{DD}=50V, I_F=20A, di/dt=100A/µs	-	50.1	-	ns
		V_{DD}=50V, I_F=20A, di/dt=200A/µs	-	41.1	-	ns
Body Diode Reverse Recovery Charge	Q_{rr}	V_{DD}=50V, I_F=20A, di/dt=100A/µs	-	81.3	-	nC
		V_{DD}=50V, I_F=20A, di/dt=200A/µs	-	122.6	-	nC
Reverse Recovery Current	I_{RRM}	V_{DD}=50V, I_F=20A, di/dt=100A/µs		2.72		A
		V_{DD}=50V, I_F=20A, di/dt=200A/µs		5.08		A

Typical Operating Characteristics

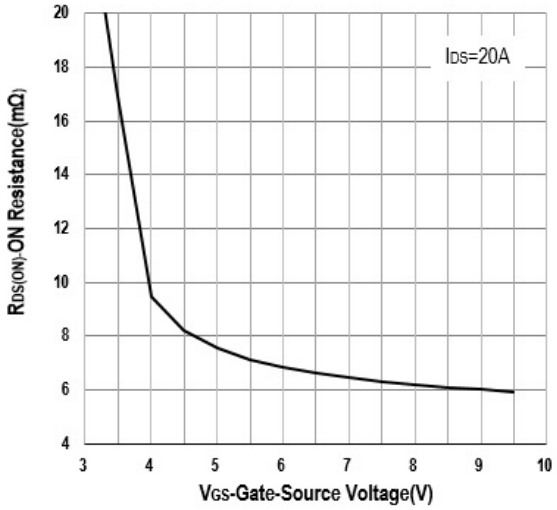
Output Characteristics



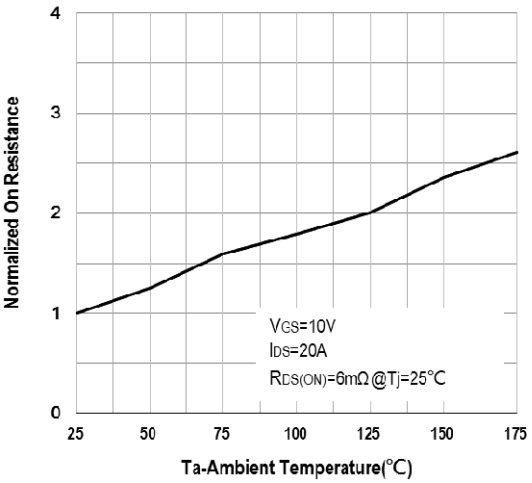
Gate Threshold Voltage



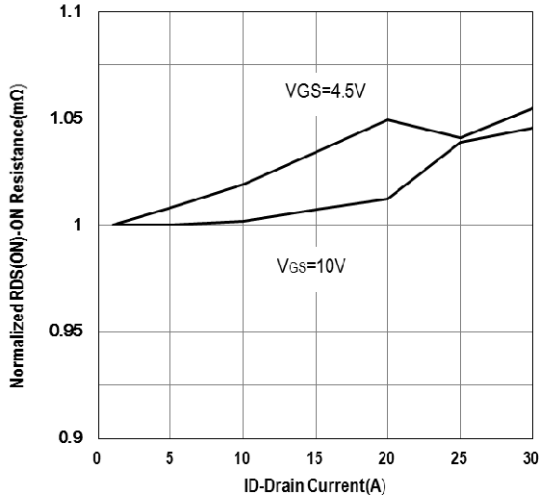
Gate-Source On Resistance



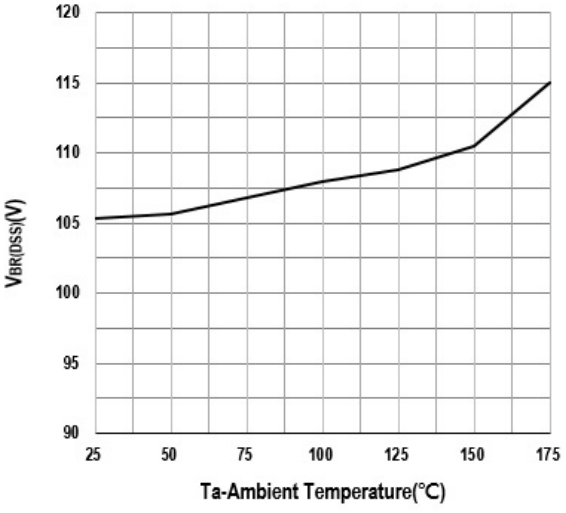
Drain-Source On Resistance



Drain-Source On Resistance

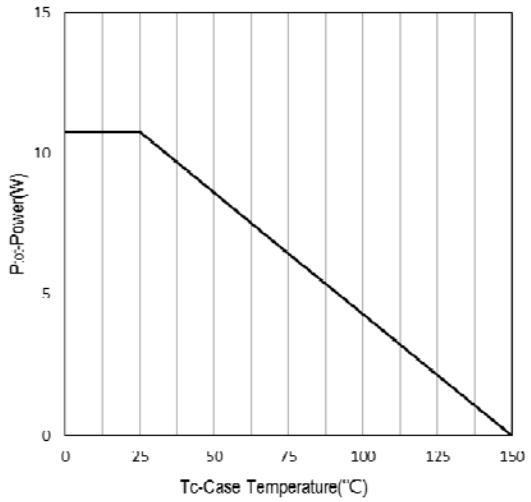


Drain-source Breakdown Voltage

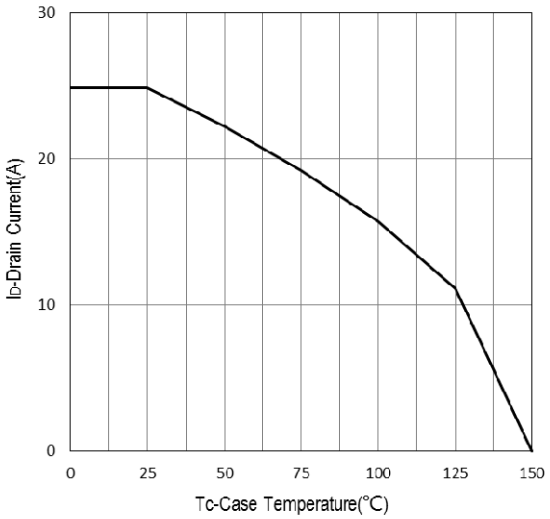


Typical Operating Characteristics (Cont.)

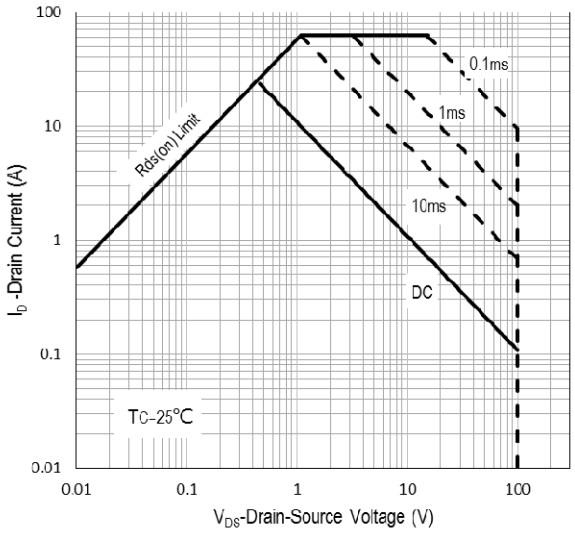
Power Dissipation



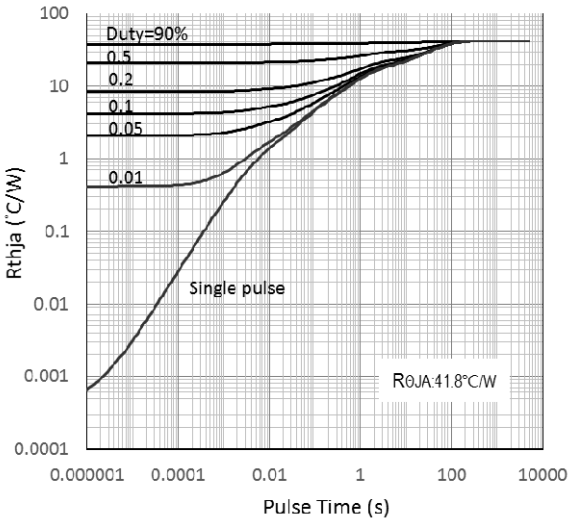
Drain Current



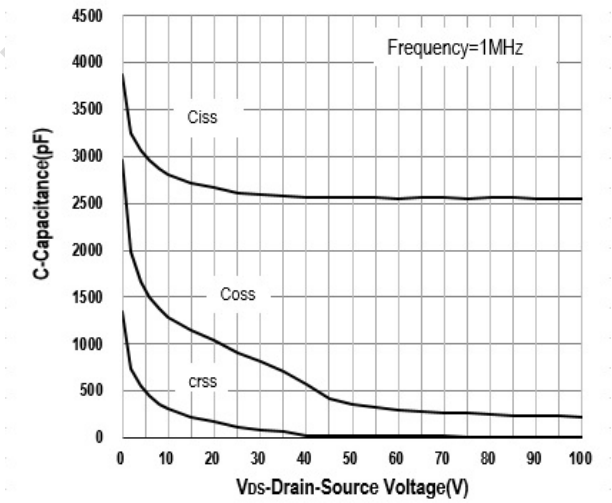
Safe Operation Area



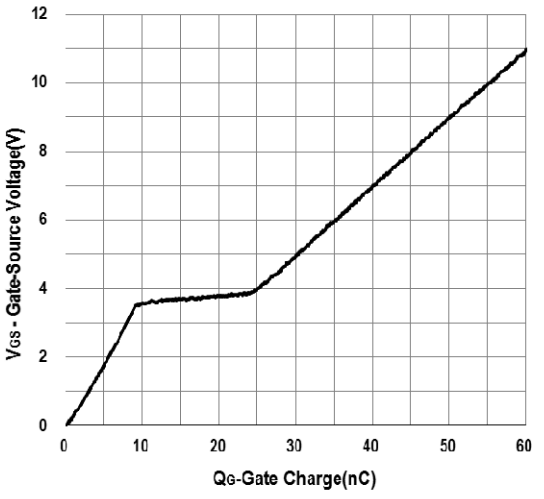
Transient Thermal Impedance



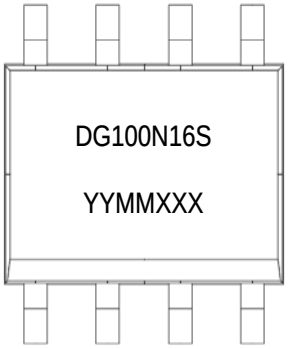
Capacitance



Gate Charge

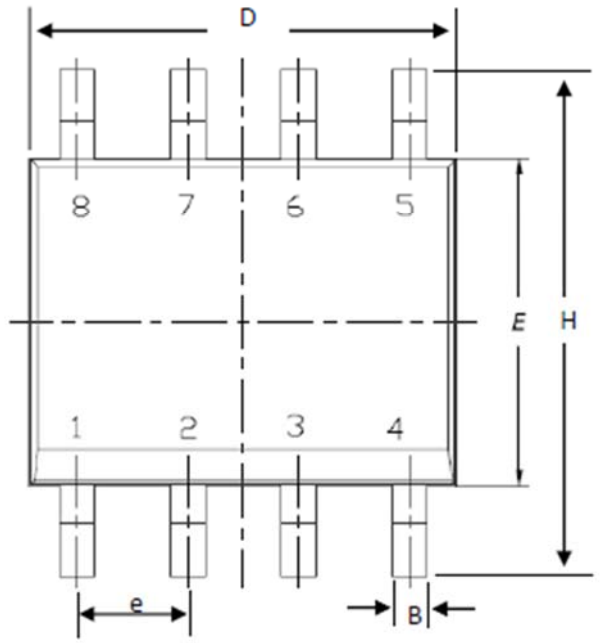


Marking Information

SOP-8 (S)	Marking Rule
Laser Marking  	Line 1：Device DG100N16S Line 2：Date Code YYMMXXX YY：Year Code MM：Month Code XXX：Serial Number

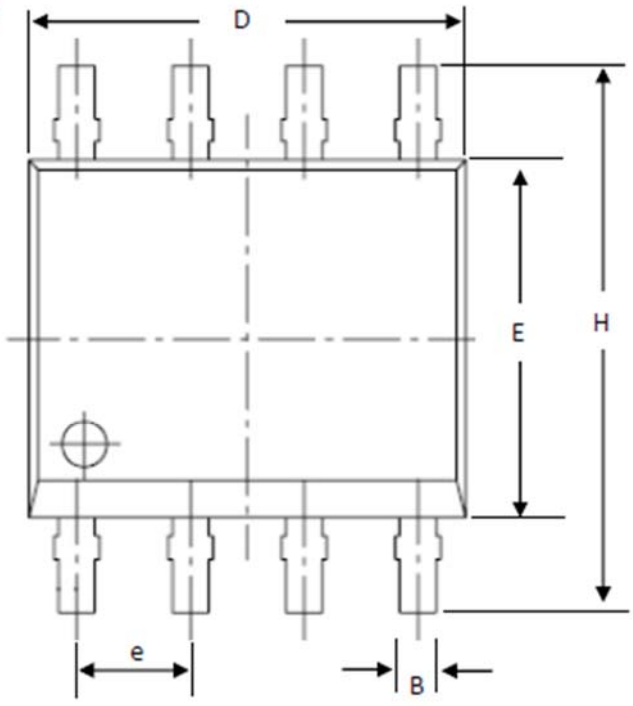
Package of Dimension

G-TYPE



Symbol	Min	Nor	Max
A	1.35	1.55	1.75
A1	0.10	0.18	0.25
B	0.31	0.41	0.51
c	0.17	0.21	0.25
D	4.80	4.90	5.00
E	3.80	3.90	4.00
e	1.27	1.27	1.27
H	5.80	6.00	6.20
L	0.40	0.84	1.27
α	0.00	4.00	8.00

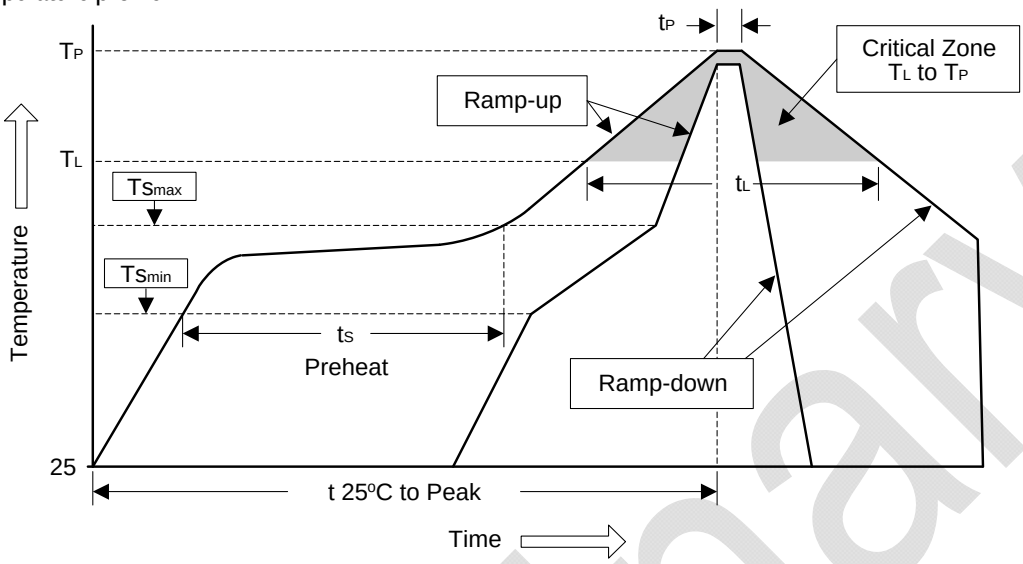
B-TYPE



Soldering Methods for Silicongear's Products

1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices

Figure 1: Temperature profile



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	<3°C/sec	<3°C/sec
Preheat - Temperature Min (Ts_{min}) - Temperature Max (Ts_{max}) - Time (min to max) (ts)	 100°C 150°C 60 to 120 sec	 150°C 200°C 60 to 180 sec
Tsmax to T_L - Ramp-up Rate	 <3°C/sec	 <3°C/sec
Time maintained above: - Temperature (T_L) - Time (t_L)	 183°C 60 to 150 sec	 217°C 60 to 150 sec
Peak Temperature (T_P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t_P)	10 to 30 sec	20 to 40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec

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